

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D T _A = +25°C
100V	220mΩ @ V _{GS} = 10V	2.3A
	250mΩ @ V _{GS} = 4.5V	2.1A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions

Features and Benefits

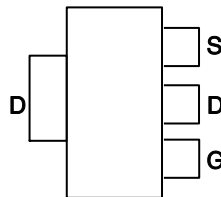
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **An Automotive-Compliant Part is Available Under Separate Datasheet ([DMN10H220LEQ](#))**

Mechanical Data

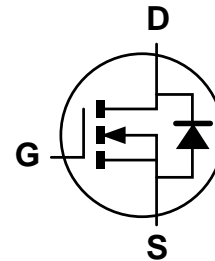
- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish - Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 ⁽³⁾
- Weight: 0.112 grams (Approximate)



Top View



Pin Out - Top View



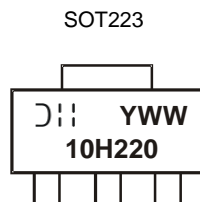
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
DMN10H220LE-13	Standard	SOT223	2,500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



D = Manufacturer's Marking
 10H220 = Marking Code
 YWW = Date Code Marking
 Y or Y = Year (ex: 7 = 2017)
 WW = Week (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	100	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (Note 5) V _{GS} = 10V	T _A = +25°C	2.3	A
	T _A = +70°C	1.8	A
	T _C = +25°C	6.2	A
	T _C = +70°C	4.9	A
Maximum Continuous Body Diode Forward Current (Note 5)	I _S	1.5	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	8	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	T _A = +25°C	1.8
		T _A = +70°C	1.1
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	69	°C/W
Total Power Dissipation (Note 5)	P _D	14	W
Thermal Resistance, Junction to Case (Note 5)	R _{θJC}	8.7	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	100	—	—	V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	µA	V _{DS} = 100V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±16V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(TH)}	1	1.7	2.5	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	155	220	mΩ	V _{GS} = 10V, I _D = 1.6A
		—	190	250		V _{GS} = 4.5V, I _D = 1.3A
Diode Forward Voltage	V _{SD}	—	0.8	1.5	V	V _{GS} = 0V, I _S = 1.1A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{iss}	—	401	—	pF	V _{DS} = 25V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	22	—		
Reverse Transfer Capacitance	C _{rss}	—	17	—		
Gate Resistance	R _g	—	2.1	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	4.1	—	nC	V _{DS} = 50V, I _D = 1.6A
Total Gate Charge (V _{GS} = 10V)	Q _g	—	8.3	—		
Gate-Source Charge	Q _{gs}	—	1.5	—		
Gate-Drain Charge	Q _{gd}	—	2	—		
Turn-On Delay Time	t _{D(ON)}	—	6.8	—	ns	V _{DS} = 50V, V _{GS} = 4.5V, R _G = 6.8Ω, I _D = 1.0A
Turn-On Rise Time	t _R	—	8.2	—		
Turn-Off Delay Time	t _{D(OFF)}	—	7.9	—		
Turn-Off Fall Time	t _F	—	3.6	—		
Reverse Recovery Time	t _{RR}	—	17	—	ns	I _S = 1.1A, di/dt = 100A/µs
Reverse Recovery Charge	Q _{RR}	—	9.8	—	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1-inch square copper plate.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to production testing.

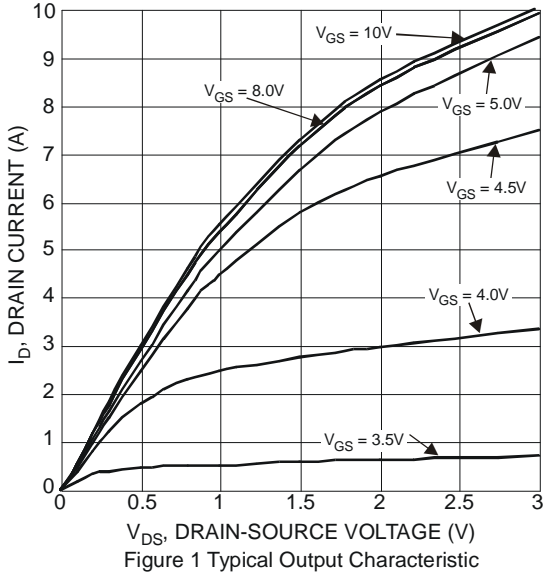


Figure 1 Typical Output Characteristic

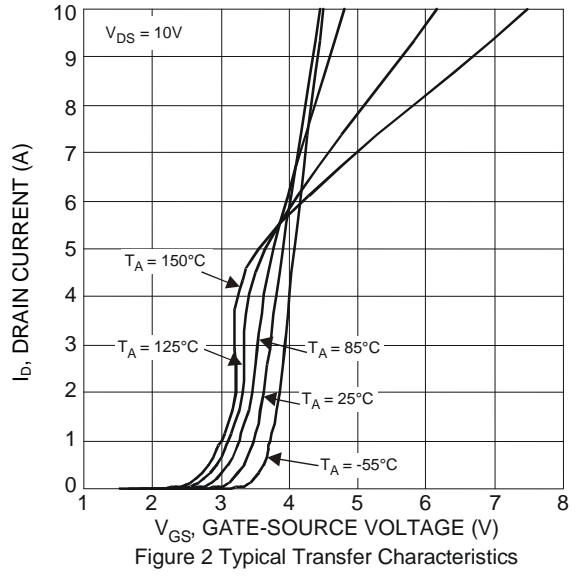


Figure 2 Typical Transfer Characteristics

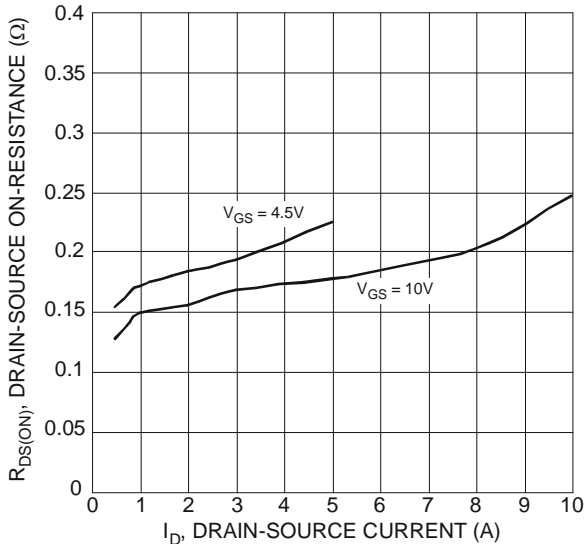


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

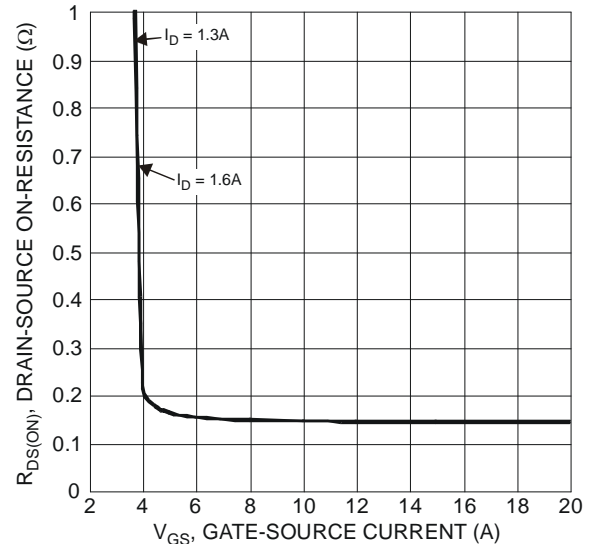


Figure 4 Typical Transfer Characteristic

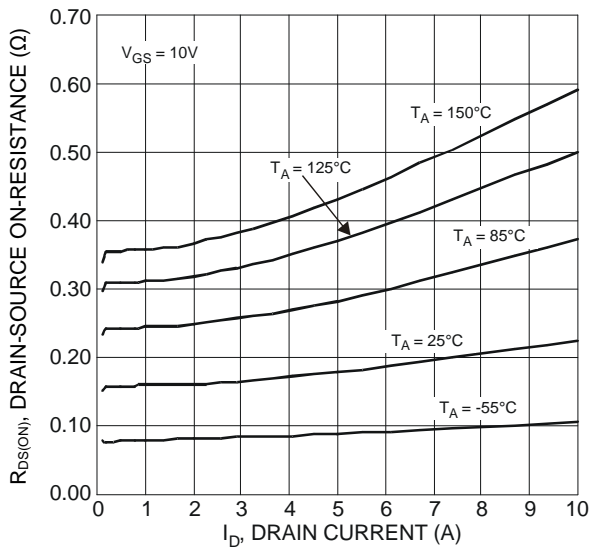


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

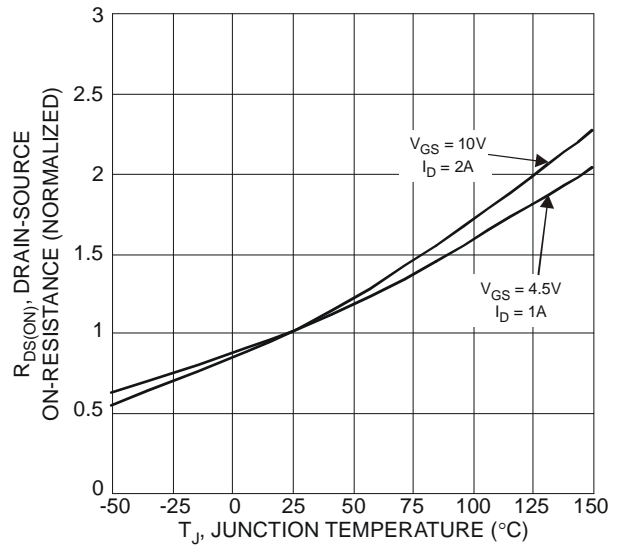


Figure 6 On-Resistance Variation with Temperature

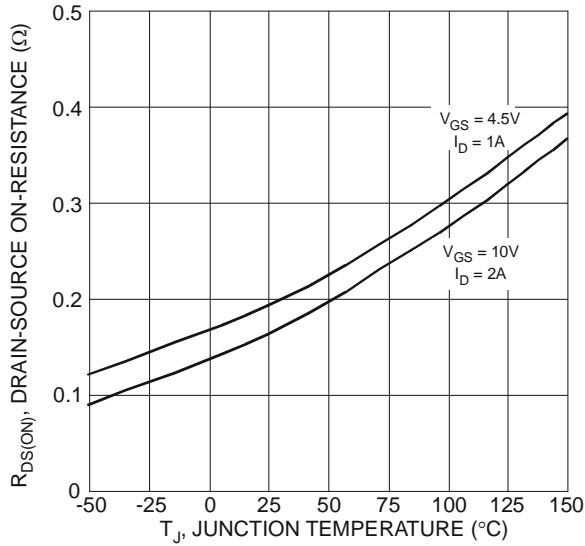


Figure 7 On-Resistance Variation with Temperature

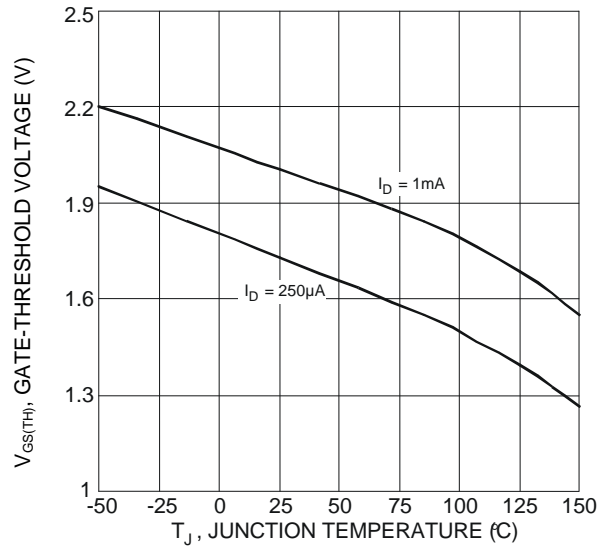


Figure 8 Gate Threshold Variation vs. Junction Temperature

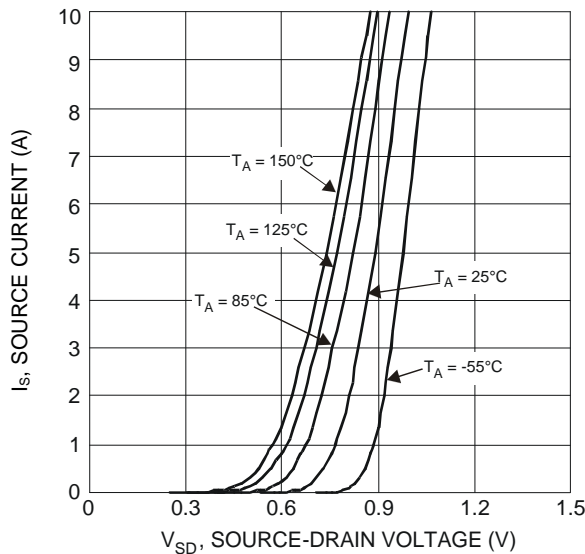


Figure 9 Diode Forward Voltage vs. Current

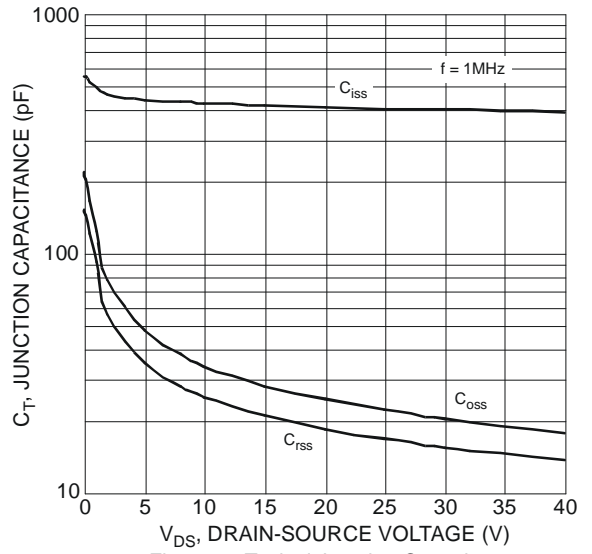


Figure 10 Typical Junction Capacitance

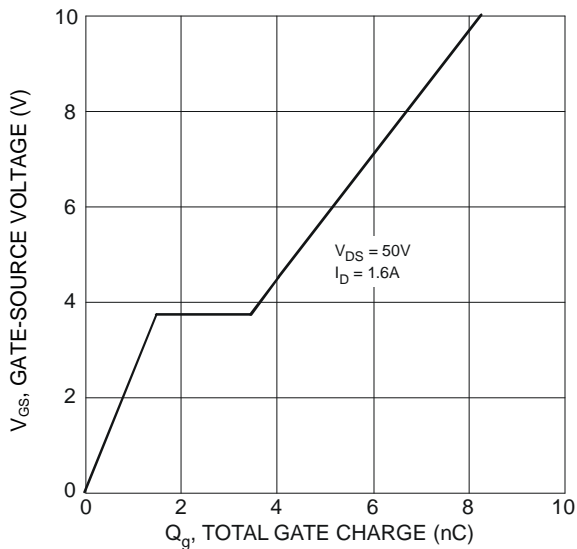


Figure 11 Gate Charge

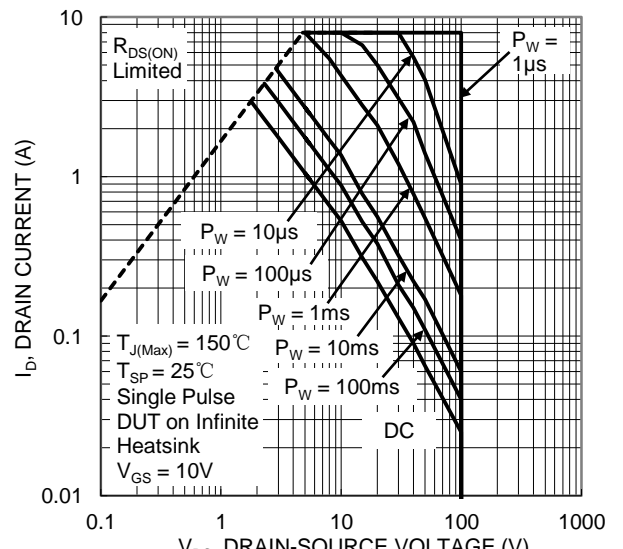


Figure 12 SOA, Safe Operation Area

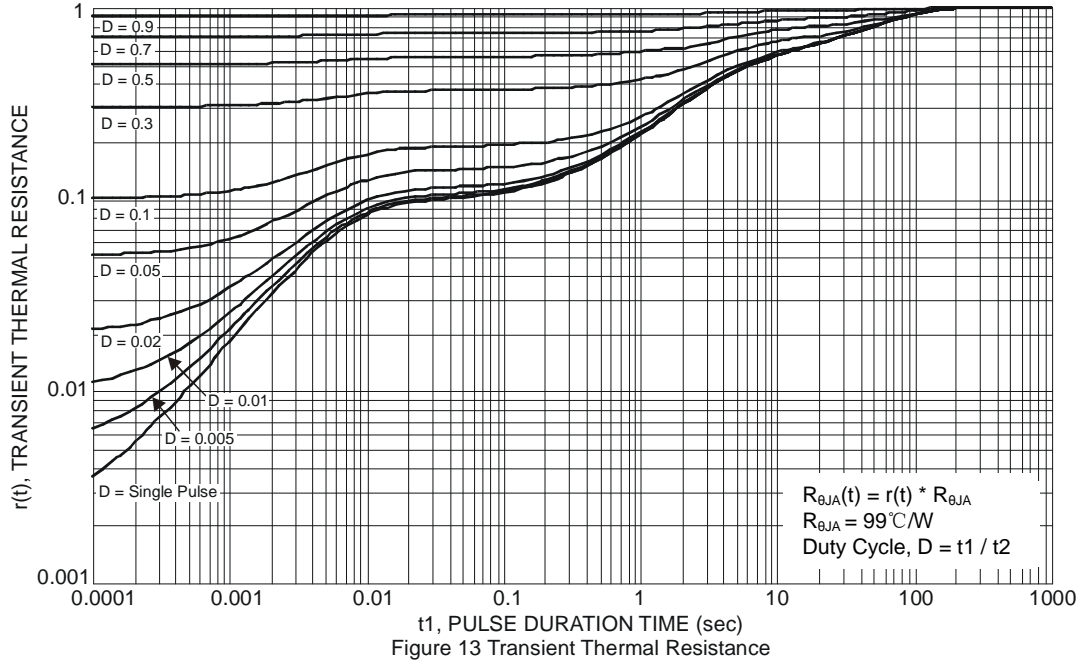
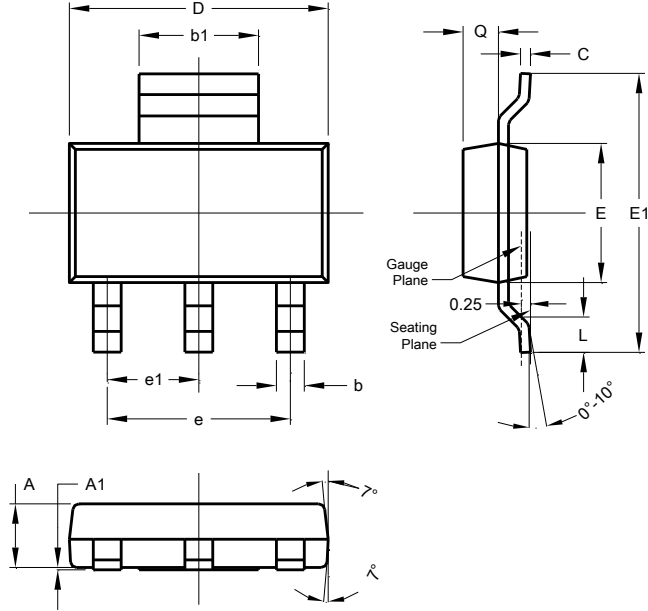


Figure 13 Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT223

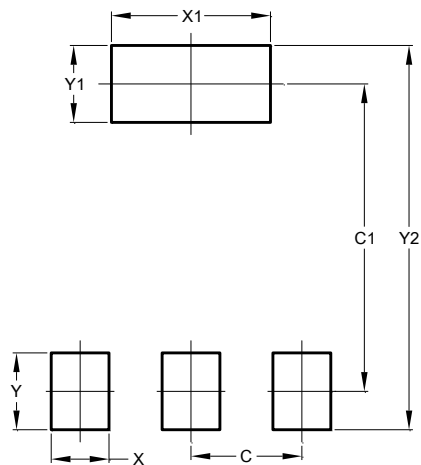


SOT223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT223



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

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